patterning and etching the aluminum so that the aluminum overlies only areas filled with copper, wherein the same mask used to pattern the dielectric layer is used to pattern the aluminum.

Please cancel claim 7, without prejudice.

9. (Twice Amended) The method of claim 6 wherein a barrier material is deposited atop the copper before the aluminum is deposited and patterned.

11. (Once amended) A method for fabricating low resistance interconnect lines in an integrated circuit, the method comprising the steps of:

patterning and etching a dielectric layer in an integrated circuit;

filling the etched areas of the dielectric layer with copper;

depositing aluminum on the copper;

patterning and etching the aluminum so that the aluminum overlies only areas filled with copper, wherein the copper has a thickness within the range of 0.3 to 2.0 μm and the aluminum has a thickness within the range of 0.5 to 3.0 μm.